
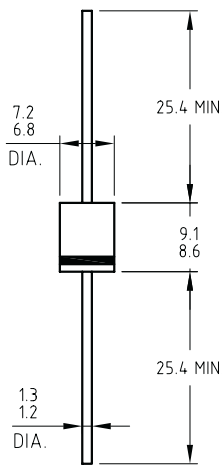


8.0 Amp. Glass Passivated Ultrafast Rectifiers

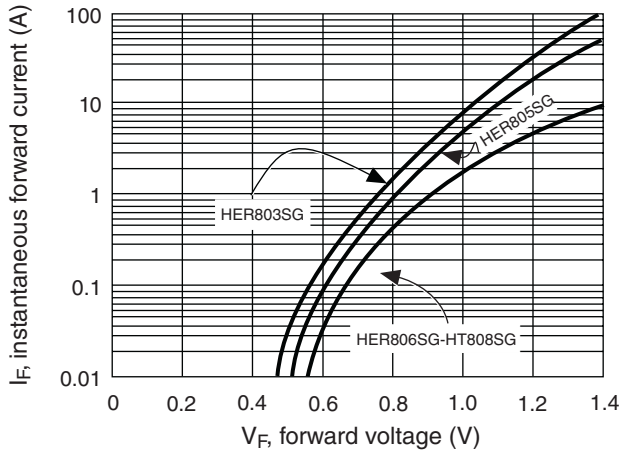
<div style="display: flex; align-items: center; gap: 10px;"> <div style="text-align: center;">  <p>RoHS COMPLIANCE</p> </div> <div style="text-align: center;"> <p>R-6</p> </div> </div> <div style="text-align: center; margin-top: 20px;">  </div> <div style="text-align: center; margin-top: 10px;"> <p>Dimensions in mm.</p> </div>	<table style="width: 100%; border-collapse: collapse;"> <tr> <td style="text-align: center; border-bottom: 1px solid black;">Voltage 200 V to 1000 V</td> <td style="text-align: center; border-bottom: 1px solid black;">Current 8.0 A</td> </tr> <tr> <td colspan="2" style="border-bottom: 1px solid black;"> <ul style="list-style-type: none"> Glass passivated chip junction. High efficiency, Low VF High current capability High reliability High surge current capability For use in low voltage, high frequency inverter, free wheeling, and polarity protection application. </td> </tr> <tr> <td colspan="2"> <p>MECHANICAL DATA</p> <ul style="list-style-type: none"> Case: Molded plastic Epoxy: UL 94V0 rate flame retardant Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed Polarity: Color band denotes cathode High temperature soldering guaranteed: 260 °C/10 seconds/9.5mm lead lengths at 2.3kg tension Mounting position: Any Weight: 1.65 grams </td> </tr> </table>	Voltage 200 V to 1000 V	Current 8.0 A	<ul style="list-style-type: none"> Glass passivated chip junction. High efficiency, Low VF High current capability High reliability High surge current capability For use in low voltage, high frequency inverter, free wheeling, and polarity protection application. 		<p>MECHANICAL DATA</p> <ul style="list-style-type: none"> Case: Molded plastic Epoxy: UL 94V0 rate flame retardant Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed Polarity: Color band denotes cathode High temperature soldering guaranteed: 260 °C/10 seconds/9.5mm lead lengths at 2.3kg tension Mounting position: Any Weight: 1.65 grams 	
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Maximum Ratings and Electrical Characteristics at 25 °C

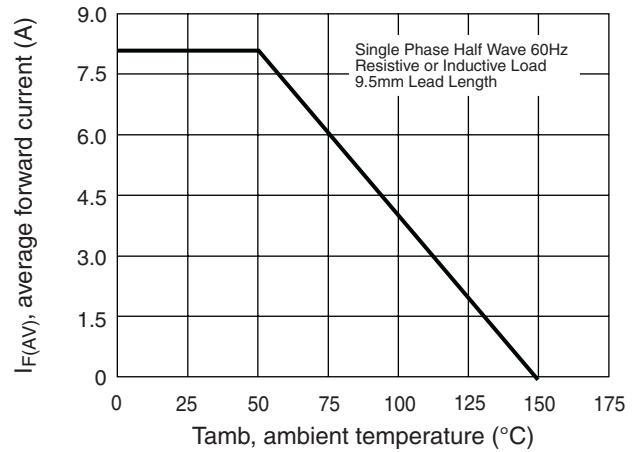
		HER 803G	HER 805G	HER 806G	HER 807G	HER 808G
V_{RRM}	Maximum Recurrent Peak Reverse Voltage (V)	200	400	600	800	1000
V_{RMS}	Maximum RMS Voltage (V)	140	280	420	560	700
V_{DC}	Maximum DC Blocking Voltage (V)	200	400	600	800	1000
$I_{F(AV)}$	Maximum Average Forward Rectified Current 9.5mm Lead Length @ $T_A = 55\text{ °C}$	8.0 A				
I_{FSM}	Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	150 A				
V_F	Maximum Instantaneous Forward Voltage at 8.0A	1.0 V	1.3 V	1.7 V		
I_R	Maximum DC Reverse Current @ $T_A = 25\text{ °C}$ at Rated DC Blocking Voltage @ $T_A = 125\text{ °C}$	10 μ A 400 μ A				
T_{rr}	Maximum Reverse Recovery Time from $I_F = 0.5A$; $I_R = 1A$; $I_{RR} = 0.25A$	50 nS		80 nS		
C_j	Typical Junction Capacitance at 1 MHz and reverse voltage of $4V_{DC}$	100 pF		65 pF		
T_j	Operating Temperature Range	-65 to + 150 °C				
T_{stg}	Storage Temperature Range	-65 to + 150 °C				

Rating And Characteristic Curves

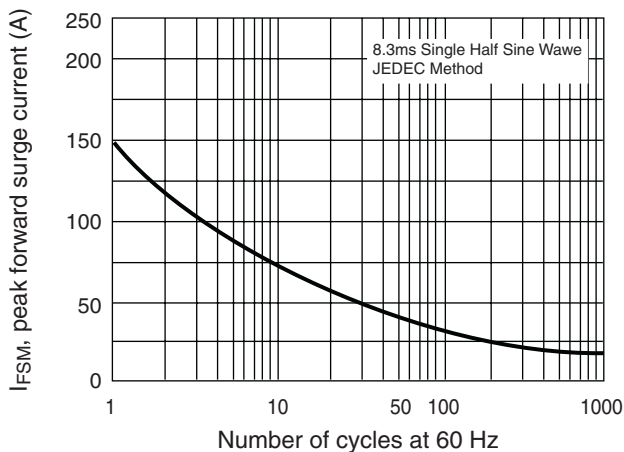
TYPICAL FORWARD CHARACTERISTIC



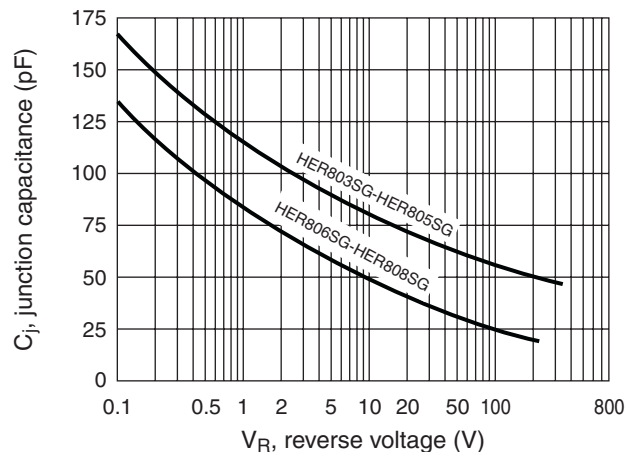
MAXIMUM FORWARD CURRENT DERATING CURVE



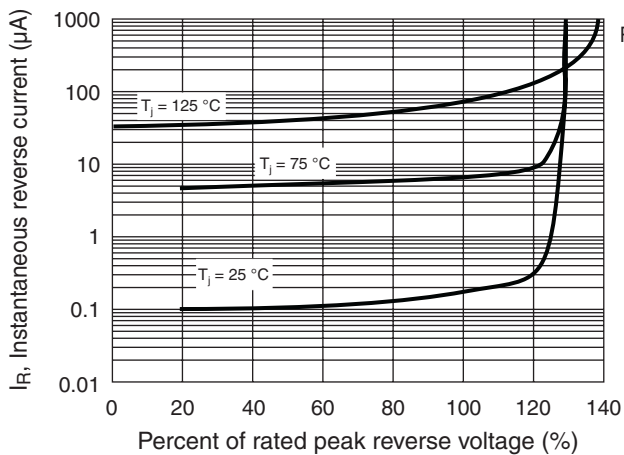
MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT



TYPICAL JUNCTION CAPACITANCE



TYPICAL REVERSE CHARACTERISTIC



REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

